

Appl. No. 10/748,784
Amdt. Dated April 3, 2008
Reply to Office Action of January 3, 2008

Attorney Docket No. 88519.0001
Customer No.: 26021

Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1-13. (Canceled)

14. (Previously presented) A light emitting device comprising:
a semiconductor layer formed on a substrate of a semiconductor device;
a ZnO transparent electrode formed on the semiconductor layer; and
an Mg-doped ZnO film disposed on a light emission side of an outer surface of
the ZnO transparent electrode that is opposite to the substrate,
wherein the semiconductor layer comprises an n-type GaN system
semiconductor layer formed on the substrate, an emission layer formed on the n-type
GaN system semiconductor layer, and a p-type GaN system semiconductor layer
formed on the emission layer.

15-26. (Canceled)